New Jersey Semi-Conductor Products, Inc.

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WW18 (NPN) & WW19 (PNP)
Silicon Complementary Transistors
High Voltage, High Current Capacity Driver

Applications:

- Drivers for Amplifiers of up to P_O = 60W

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 80V
Collector–Emitter Voltage, V_{CEO} 80V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C
  Continuous 700mA
  Pulse (Note 1) 1A
Collector Dissipation, P_C 1W
Junction Temperature, T_J ..... +135°C
Storage Temperature Range, T_{stg} ..... –55° to +135°C

Note 1. P_W = 20ms, Duty Cycle = 1/2

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 2mA	80	–	–	V
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 50μA	80	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 50μA	5	–	–	V
Collector Cutoff Current	I_{CBO}	V_{CB} = 50V	–	–	0.5	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V	–	–	0.5	μA
DC Current Gain	h_{FE}	V_{CE} = 3V, I_C = 100mA	120	–	270	
Collector Saturation Voltage	$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA	–	200	400	mV
Transition Frequency 18	f_T	V_{CE} = 10V, I_C = 50mA	–	120	–	MHz
19			–	100	–	MHz
Output Capacitance 18	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	–	10	–	pF
19			–	14	20	pF

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Quality Semi-Conductors

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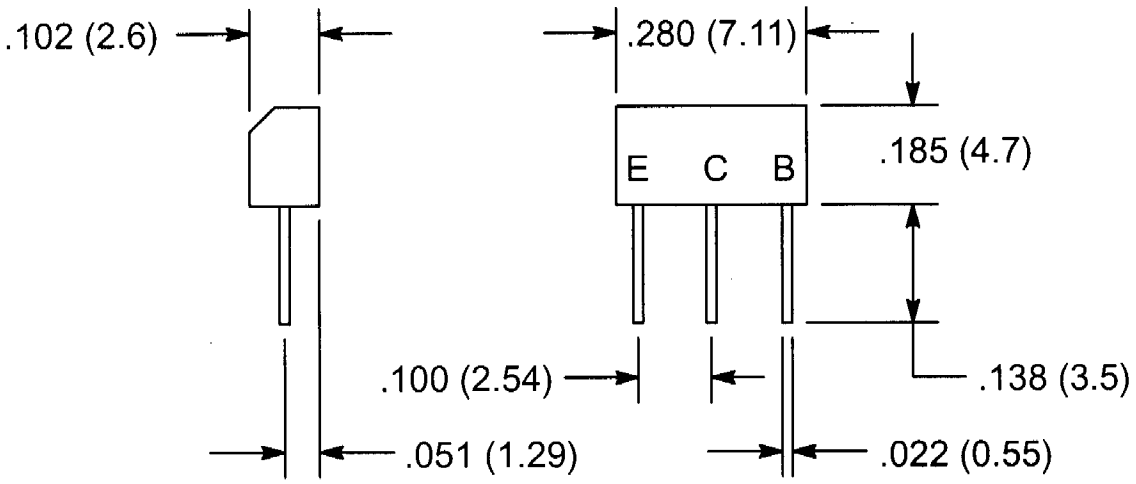

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